

# **isc Silicon NPN Power Transistor**

# **BU2532AW**

# **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= 800V (Min)
- · High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

• Designed for use in horizontal deflection circuits of high resolution monitors.

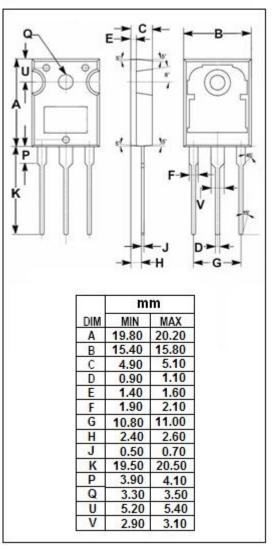
# PIN 1. BASE 2.COLLECTOR 3. BMITTER 1 2 3 TO-247 package

# ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CES</sub>	Collector- Emitter Voltage(V <sub>BE</sub> = 0)	1500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	7.5	V
Ic	Collector Current- Continuous	16	Α
I <sub>CM</sub>	Collector Current-Peak	40	А
I <sub>B</sub>	Base Current- Continuous	10	Α
I <sub>BM</sub>	Base Current-Peak	15	Α
Pc	Collector Power Dissipation  @ T <sub>C</sub> =25°C	125	W
TJ	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT	
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.0	°C/W	





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### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT				
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	800			V				
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7.5			V				
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 1.17A			5.0	V				
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 1.17A			0.97	V				
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V; V <sub>BE</sub> = 0 V <sub>CE</sub> = 1500V; V <sub>BE</sub> = 0; T <sub>C</sub> =125°C			1.0 2.0	mA				
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7.5V; I <sub>C</sub> = 0			1.0	mA				
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	9		27					
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 7A; V <sub>CE</sub> = 5V	6		12.5					

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